



IRFB4233PBF Information

Part Number IRFB4233PBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 230V 56A TO-220AB

TO-220-3 **Package**

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com For Reference Only

E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IRFB4233PBF Specifications

Manufacturer Part NumberIRFB4233PBFManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-220-3SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)230VCurrent - Continuous Drain (Id) @ 25°C56A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250µAGate Charge (Qg) (Max) @ Vgs170nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5510pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)370W (Tc)Rds On (Max) @ Id, Vgs37 mOhm @ 28A, 10VOperating Temperature-40°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3Report errors?		
Category Discrete Semiconductor Products Package TO-220-3 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 230V Current - Continuous Drain (Id) @ 25°C 56A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 170nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5510pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 370W (Tc) Rds On (Max) @ Id, Vgs 37 mOhm @ 28A, 10V Operating Temperature -40°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Manufacturer Part Number	IRFB4233PBF
Package TO-220-3 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 230V Current - Continuous Drain (Id) @ 25°C 56A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 170nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5510pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 370W (Tc) Rds On (Max) @ Id, Vgs 37 mOhm @ 28A, 10V Operating Temperature -40°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Manufacturer	Infineon Technologies
Package TO-220-3 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 230V Current - Continuous Drain (Id) @ 25°C 56A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 170nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5510pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 370W (Tc) Rds On (Max) @ Id, Vgs 37 mOhm @ 28A, 10V Operating Temperature -40°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Category	Discrete Semiconductor Products
SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)230VCurrent - Continuous Drain (Id) @ 25°C56A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs170nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5510pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)370W (Tc)Rds On (Max) @ Id, Vgs37 mOhm @ 28A, 10VOperating Temperature-40°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)230VCurrent - Continuous Drain (Id) @ 25°C56A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs170nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5510pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)370W (Tc)Rds On (Max) @ Id, Vgs37 mOhm @ 28A, 10VOperating Temperature-40°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)230VCurrent - Continuous Drain (Id) @ 25°C56A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs170nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5510pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)370W (Tc)Rds On (Max) @ Id, Vgs37 mOhm @ 28A, 10VOperating Temperature-40°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	HEXFET?
Drain to Source Voltage (Vdss)230VCurrent - Continuous Drain (Id) @ 25°C56A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs170nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5510pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)370W (Tc)Rds On (Max) @ Id, Vgs37 mOhm @ 28A, 10VOperating Temperature-40°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 170nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5510pF @ 25V Vgs (Max) ### ### ### ### ### ### ### ### ### #	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Sty @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 37 mOhm @ 28A, 10V Operating Temperature Au°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB	Drain to Source Voltage (Vdss)	230V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 5V @ 250μA 170nC @ 10V 1	Current - Continuous Drain (Id) @ 25°C	56A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 5510pF @ 25V Vgs (Max) ±30V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 37 mOhm @ 28A, 10V Operating Temperature -40°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case TO-220-3	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 370W (Tc) Rds On (Max) @ Id, Vgs 37 mOhm @ 28A, 10V Operating Temperature -40°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Gate Charge (Qg) (Max) @ Vgs	170nC @ 10V
FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -40°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	5510pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 37 mOhm @ 28A, 10V Operating Temperature -40°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs $ 37 \text{ mOhm } @ 28A, 10V $ Operating Temperature $ -40^{\circ}\text{C} \sim 175^{\circ}\text{C} \text{ (TJ)} $ Mounting Type $ \text{Through Hole} $ Supplier Device Package $ \text{TO-220AB} $ Package / Case $ \text{TO-220-3} $	FET Feature	-
Operating Temperature -40°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	370W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	37 mOhm @ 28A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-40°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

IRFB4233PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFB4233PBF Payment Methods



















IRFB4233PBF Shipping Methods













If you have any question about IRFB4233PBF, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com